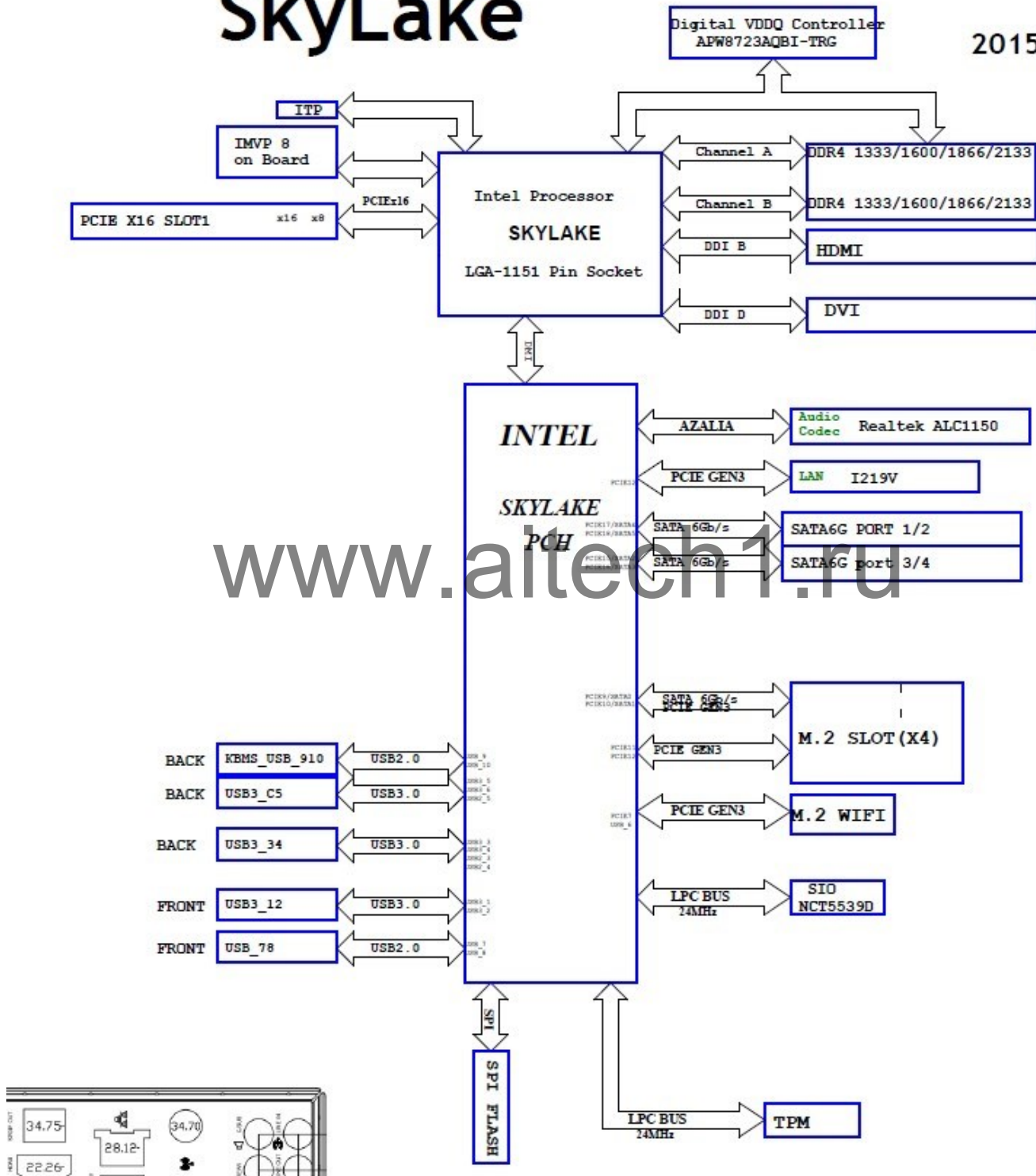


## 1. BLOCK DIAGRAM

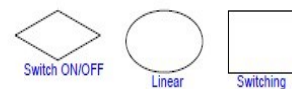
## SkyLake

2015.12



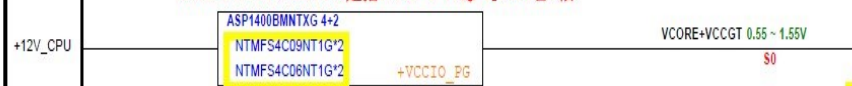
## 2. POWER FLOW

(98) power flow update成 power線路:RAPHAEL\_R100\_10071800.DSN

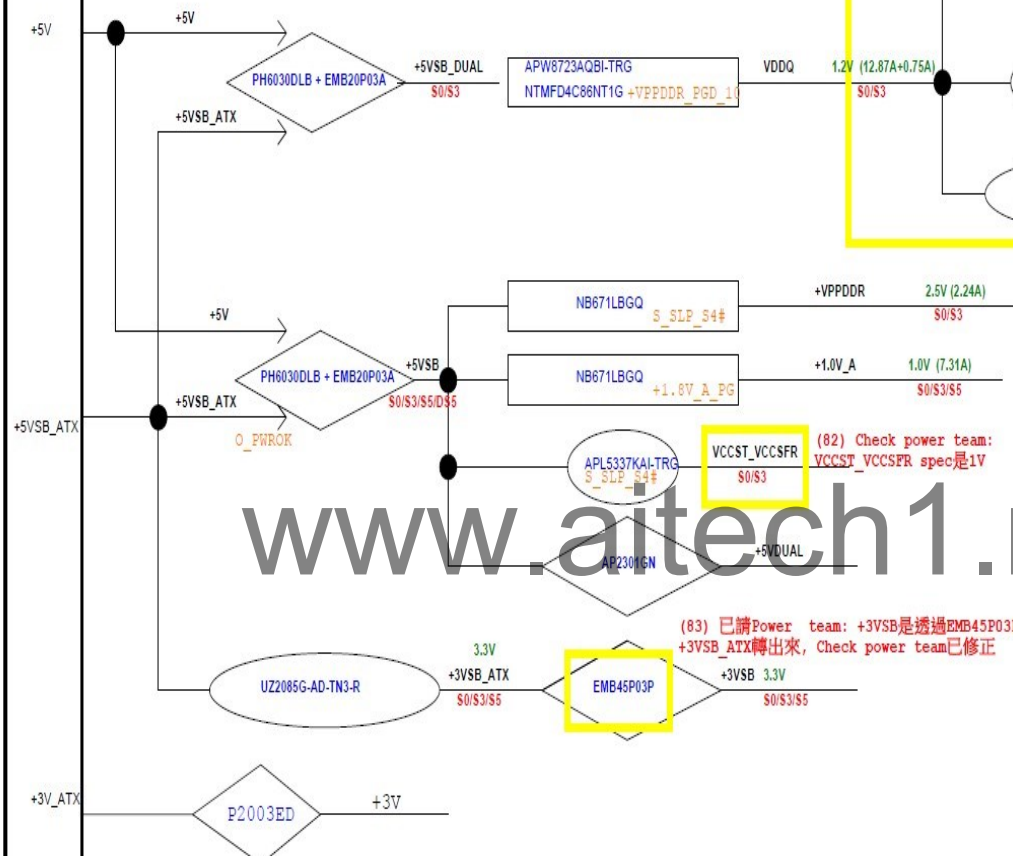
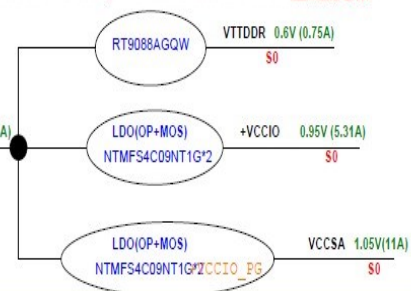


Control signal  
Power Rail

(71) Check power team:  
VCORE NTMFS4C09NT1G\*2是指Voore & GT每 1phase各1顆.



(42) check VCCIO, VCCSA FLOW CHAT已經更新.



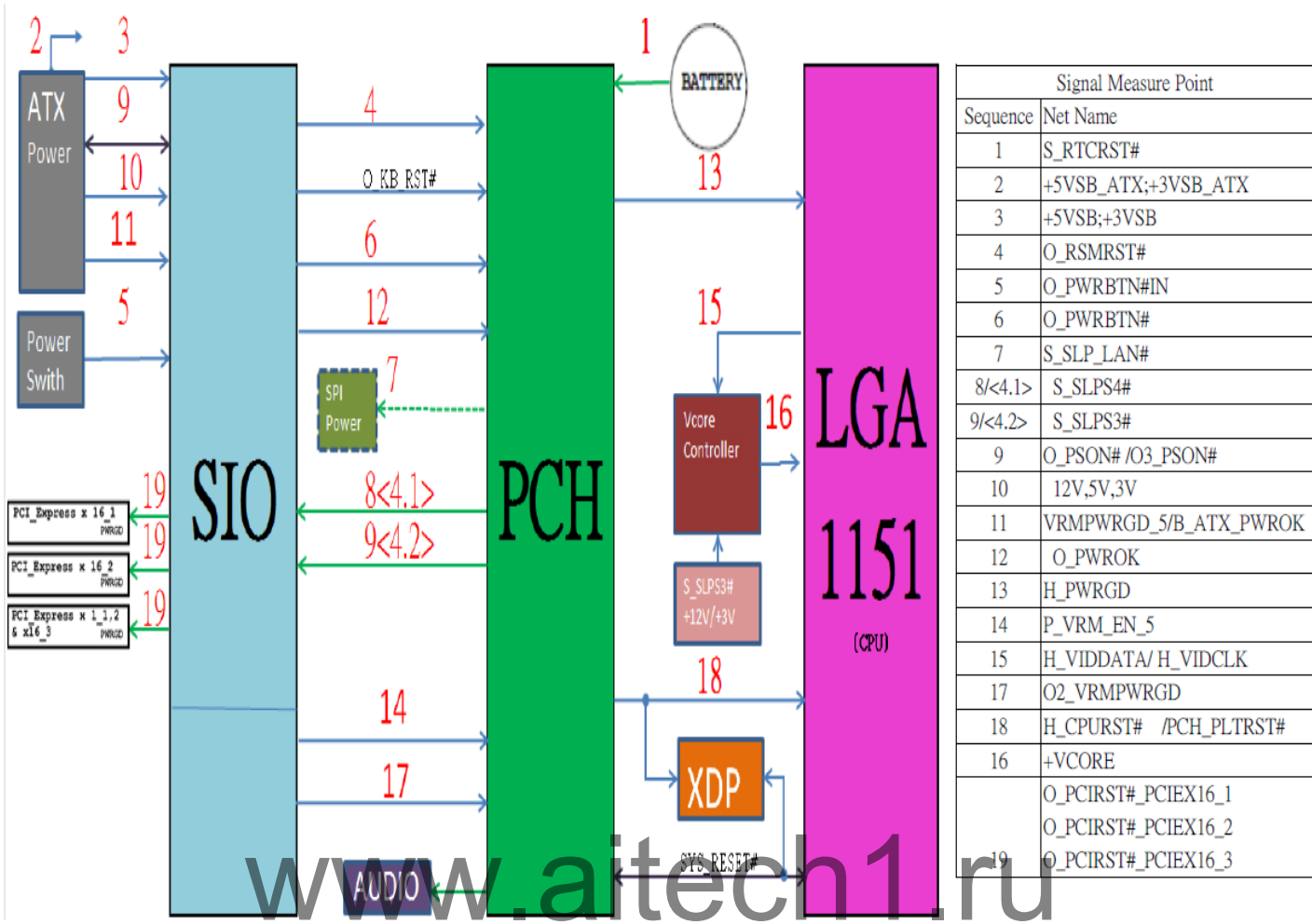
(82) Check power team:  
VCCST\_VCCSFR spec是1V

(83) 已請Power team: +3VSB是透過EMB45P03P從  
+3VSB\_ATX轉出來, Check power team已修正

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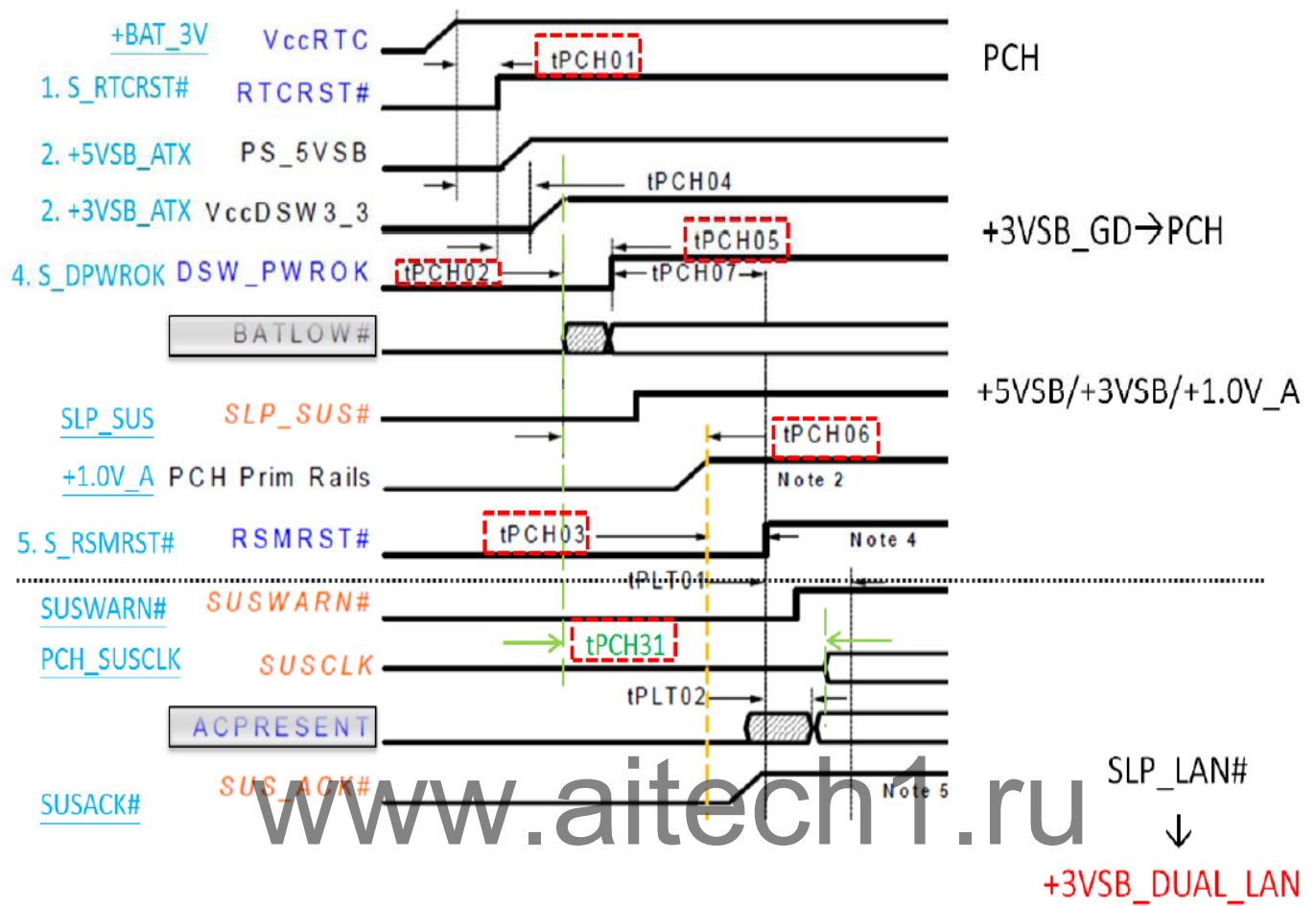
ASUS		Title: POWER FLOW CHART	
ASUSTek COMPUTER INC.		Engineer: Bing-jie Wang	
Size	Project Name	Rev	
A3		1.05	
Date: Tuesday, January 28, 2020 11:13 AM		SILVER LAKE CHIPSET DEMO	

3. POWER ON SEQUENCE



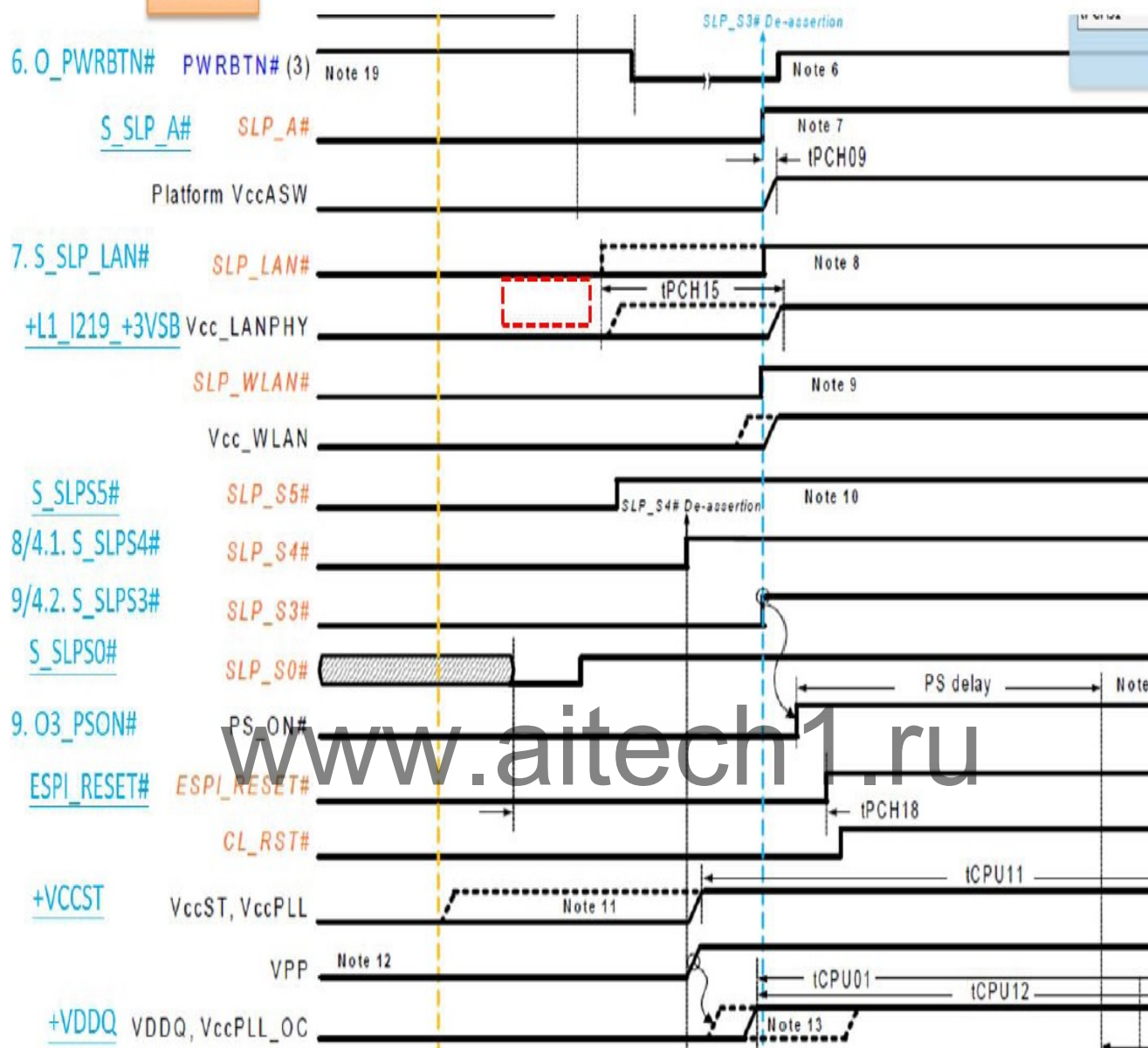
#### 4. Timing Diagram for G3 to S5

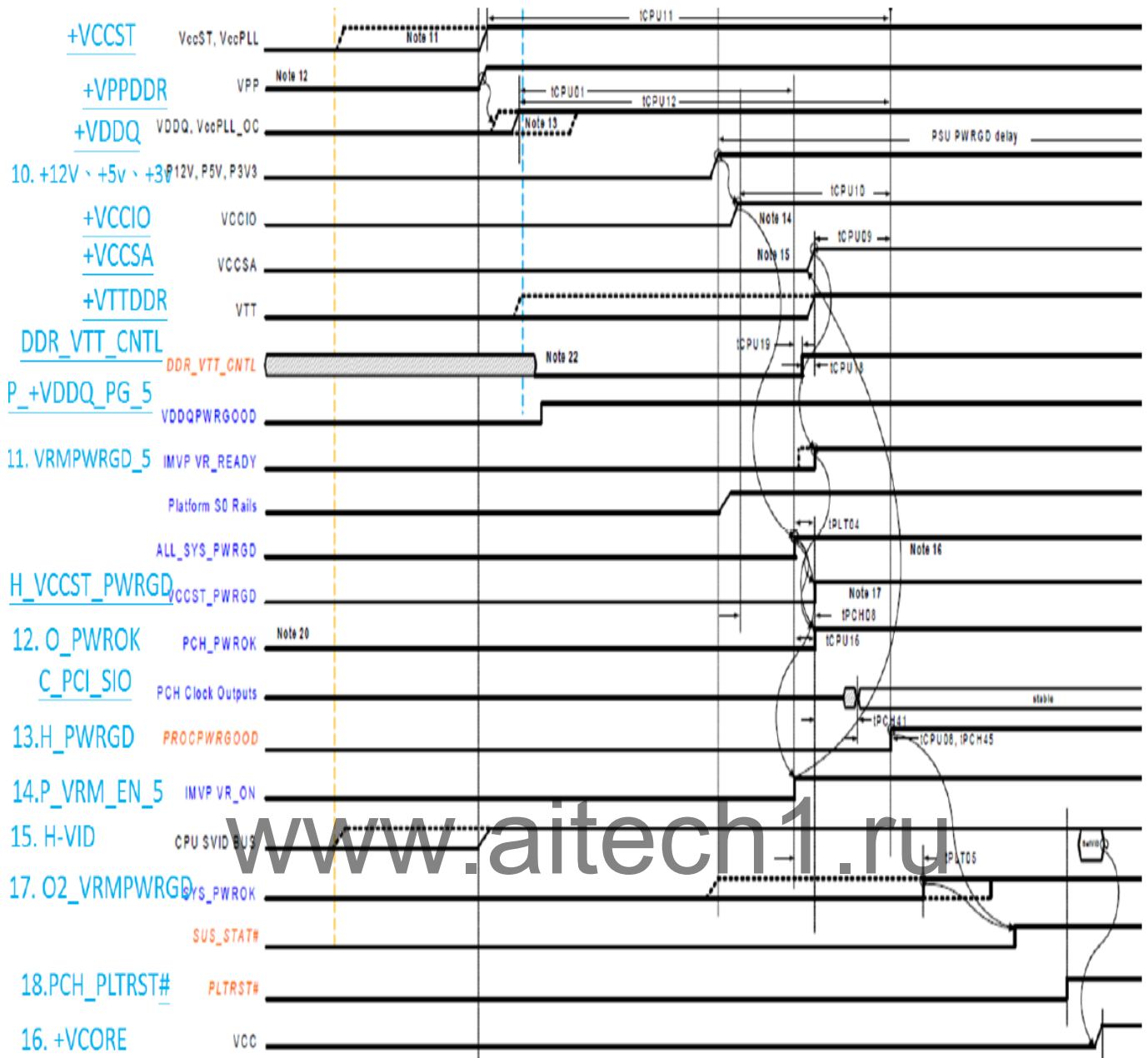
G3→S5



## Timing Diagram for S5 to S0/M0

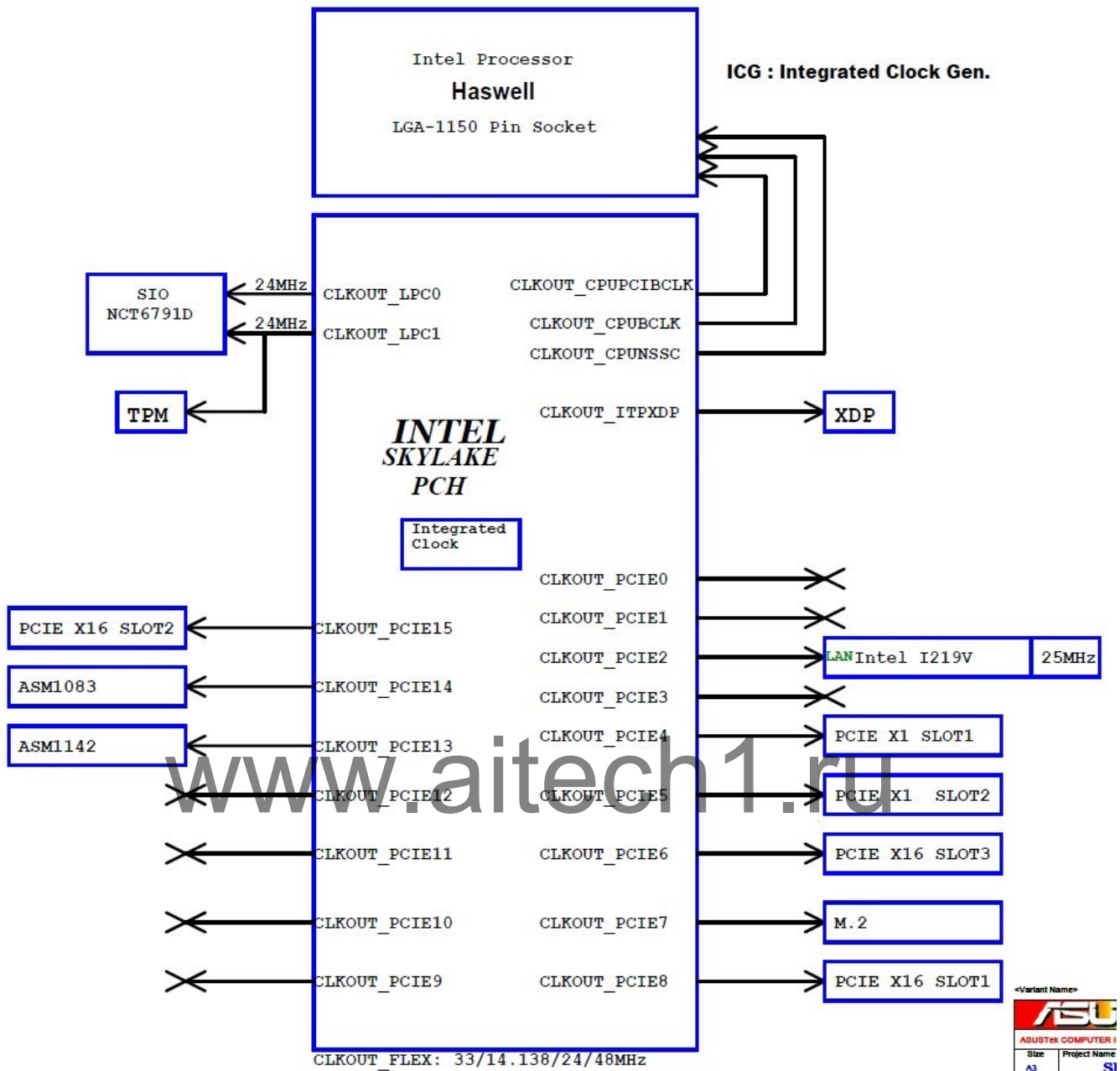
S5→S0







## 5. Frequency Flow



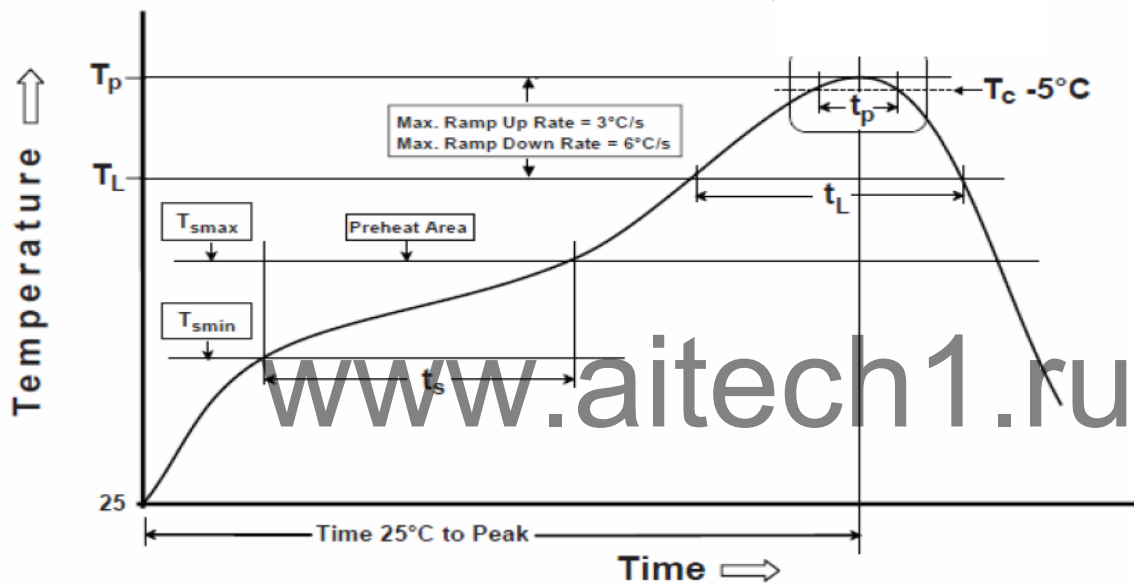
## 6. Socket reflow profile

Profile Feature	SMD Pb-Free Assembly	DIP Pb-Free Assembly	SMT Component Vendor Spec	DIP Component Vendor Spec
Preheat/Soak				
Temperature Min (T <sub>min</sub> )	150 °C	80 °C	150 °C	135 °C
Temperature Max (T <sub>max</sub> )	200 °C	135 °C	200 °C	need endure 80 seconds
Time (t <sub>s</sub> ) from (T <sub>min</sub> to T <sub>max</sub> )	120 seconds	120 seconds	need endure 120 seconds	
Ramp-up rate (TL to Tp)	3 °C/second max.	3 °C/second max.	need endure 3 °C/second max.	need endure 3 °C/second max.
Liquidous temperature (TL)	217 °C	NA	217 °C	NA
Time (t <sub>L</sub> ) maintained above TL	90 seconds		need endure 90 seconds	
Peak package body temperature (Tp)	260 °C	270 °C	260 °C	270 °C
Time (t <sub>p</sub> )* within 5 °C of the specified classification temperature (Tc), see Figure 1-1.	10* seconds	6* seconds	need endure 10* seconds	need endure 6* seconds
Ramp-down rate (Tp to TL)	6 °C/second max.	6 °C/second max.	need endure 6 °C/second max.	need endure 6 °C/second max.
Time 25 °C to peak temperature	8 minutes max.	8 minutes max.	8 minutes max.	8 minutes max.

Note 1: All temperatures refer to the center of the package, measured on the package body surface that is facing up during assembly reflow (e.g., live-bug). If parts are reflowed in other than the normal live-bug assembly reflow orientation (i.e., dead-bug), Tp shall be within  $\pm 2$  °C of the live-bug Tp and still meet the Tc requirements, otherwise, the profile shall be adjusted to achieve the latter. To accurately measure actual peak package body temperatures refer to JEP140 for recommended thermocouple use.

2. DIP Plastic heat resistance capability :

- (1) Direct contact 270°C, 6 seconds
- (2) In-direct contact 230°C, 5 seconds
- (3) no contact 130°C, 5 seconds





## 7. Lead-Free Rework Thermo profile Graphic for BGA & Chipset



Except for body temp, all temperatures are measured with thermo couples inside solder joints, for better accuracy

### Primary Factors for Successful Rework:

- Flux formulation and solder paste formulation and volume
- A capable thermal reflow profile
- Proper PCB pad solder preparation/wicking (clean-up of the residual solder

from the PCB pads)

**Caution: Always remove batteries and thermal solutions following the system design disassembly process steps prior to BGA rework to avoid damaging the BGA.**

View this Intel®BGA / Socket Rework Video (10 minutes in length):

<http://link.brightcove.com/services/player/bcpid1409165005001?bckey=AQ~~,AAAQwZd9wk~,X1Exj3sUi-03b71FGkEmVWbi4T4yGcor&bctid=1519232885001>

## 8. MB Baking Time: 120 °C, 8 hours

### BGA Baking Time:

**5.2 Floor Life** The floor life of SMDs per Table 5-1 will be modified by environmental conditions other than 30 °C/60% RH. Refer to Clause 7 to determine maximum allowable time before rebake would be necessary. If partial lots are used, the remaining SMD packages must be resealed or placed in safe storage within one hour of bag opening (see 5.3). If one hour exposure is exceeded, refer to 4.1.

**Table 5-1 Moisture Classification Level and Floor Life per J-STD-020**

Level	Floor Life (out of bag) at factory ambient $\pm 30^{\circ}\text{C}/60\%$ RH or as stated
1	Unlimited at $\pm 30^{\circ}\text{C}/85\%$ RH
2	1 year
2a	4 weeks
3	168 hours
4	72 hours
5	48 hours
5a	24 hours
6	Mandatory bake before use. After bake, must be reflowed within the time limit specified on the label

**Supplier Bake: Default Baking Times Used Prior to Dry-Pack that were Exposed to Conditions  $\pm 60\%$  RH (“MET” = 24 h )**

Package Body Thickness	Level	Bake @ $125^{\circ}\text{C} +10/-0^{\circ}\text{C}$	Bake @ $150^{\circ}\text{C} +10/-0^{\circ}\text{C}$
$\leq 1.4\text{ mm}$	2	7 hours	3 hours
	2a	8 hours	4 hours
	3	16 hours	8 hours
	4	21 hours	10 hours
	5	24 hours	12 hours
	5a	28 hours	14 hours
$> 1.4\text{ mm}$ $\leq 2.0\text{ mm}$	2	18 hours	9 hours
	2a	23 hours	11 hours
	3	43 hours	21 hours
	4	48 hours	24 hours
	5	48 hours	24 hours
$> 2.0\text{ mm}$ $\leq 4.5\text{ mm}$	5a	48 hours	24 hours
	2	48 hours	24 hours
	2a	48 hours	24 hours
	3	48 hours	24 hours
	4	48 hours	24 hours
	5	48 hours	24 hours
	5a	48 hours	24 hours

**Note 1:** If baking of packages  $> 4.5\text{ mm}$  thick is required see appendix B.

**Note 2:** The bake times specified are conservative for packages without blocking planes or stacked die. For a stacked die or BGA package with internal planes that impede moisture diffusion the actual bake time may be longer than that required in Table 4-2 if packages have had extended exposure to factory ambient before bake. Also the actual bake time may be reduced if technically justified. The increase or decrease in bake time **shall** be determined using the procedure in JEDEC JESD22-A120 (i.e.,  $< 0.002\%$  weight loss between successive readouts) or per critical interface concentration calculations.

## 9. Voltage Measure Point

Voltage Measure Point		
Station	Net Name	Diode resistance
OQ760	+3VSB_ATX	327
PL706	+5VSB	500
PL201	VCCGT	463
EATX12V	+12V_CPU	747
TPM	+3VSB	293
PC956	VTT_DDR	423
EATXPWR	+5VSB_ATX	600
PL903	+5VSB_DUAL	508
EATXPWR	+12V	496
EATXPWR	+5V	476
PQ403	+3V	321

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## 10.Signal Measure Point

		Signal Measure Point	
Station	Sequence	Net Name	Diode resistance
SR120	1	S_RTCRST#	783
SR121		S_SRTCST#	783
NA	2	AC Power Switch ON	NA
PL706	3	+5VSB	500
TPM		+3VSB	293
SR1627	3.1	S_RSMRST#	18
SR1627	4	O_RSMRST#	18
O1R14	5	PWRBTN#	839
O1R90	6	O_IOPWRBTN#	511
PR689	7/4.2	S_SLP_S3#	503
NA	7	S_SLP_A#	NA
NA	7.1	S_SLP_LAN#	NA
PR518	8/4.1	S_SLP_S4#	504
EATXPWR	9	ATX_PSON#_R	549
EATXPWR	10	12V	496
EATXPWR		5V	476
PQ403		3V	321
EATXPWR	11	P_PWROK_PS	NA
PR625	12	O_PWROK	35
SR75	13	H_CPUPWRGD	445
HR210	14	H_SVID_DATA	506
PR109		H_SVID_CLK	511
PC189	15	VCORE	420
SQ6	16	P_VR_READY_10	536
TPM	17	S_PLTRST#	501
ESDC3	18	H_CPURST#	430
OR770	19	O_X1__RST#	584
XC71		O_X16_RST#	588